



DC COMPONENTS CO., LTD.

DISCRETE SEMICONDUCTORS

BF422

TECHNICAL SPECIFICATIONS OF NPN EPITAXIAL PLANAR TRANSISTOR

Description

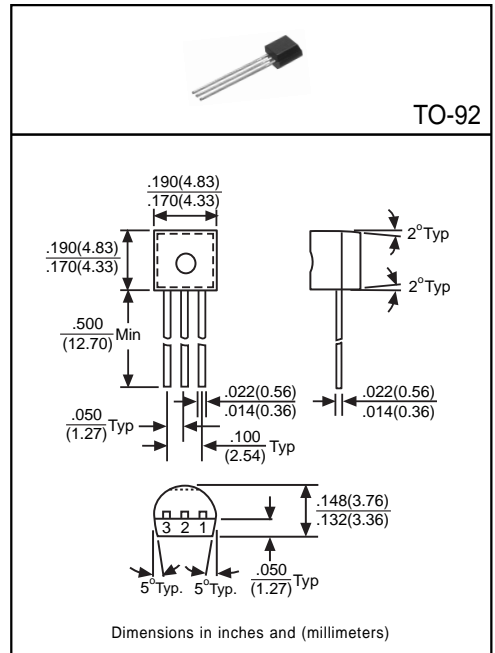
Designed for video B-class power stages in TV receivers.

Pinning

- 1 = Emitter
- 2 = Collector
- 3 = Base

Absolute Maximum Ratings (T_A=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	250	V
Collector-Emitter Voltage	V _{CEO}	250	V
Emitter-Base Voltage	V _{EB0}	5	V
Collector Current	I _C	50	mA
Total Power Dissipation	P _D	830	mW
Junction Temperature	T _J	+150	°C
Storage Temperature	T _{STG}	-55 to +150	°C



Electrical Characteristics

(Ratings at 25°C ambient temperature unless otherwise specified)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV _{CB0}	250	-	-	V	I _C =100μA
Collector-Emitter Breakdown Voltage	BV _{CEO}	250	-	-	V	I _C =1mA
Emitter-Base Breakdown Voltage	BV _{EB0}	5	-	-	V	I _E =10μA
Collector Cutoff Current	I _{CB0}	-	-	0.1	μA	V _{CB} =200V
Emitter Cutoff Current	I _{EB0}	-	-	10	μA	V _{EB} =5V
Collector-Emitter Saturation Voltage ⁽¹⁾	V _{CE(sat)}	-	-	0.6	V	I _C =30mA, I _B =3mA
DC Current Gain ⁽¹⁾	h _{FE}	50	-	-	-	I _C =25mA, V _{CE} =20V
Transition Frequency	f _T	60	-	-	MHz	I _E =10mA, V _{CE} =10V, f=100MHz

(1) Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%